

# Z0103NA0

4Q Triac

4 April 2014

Product data sheet

## 1. General description

Planar passivated very sensitive gate four quadrant triac in a SOT54 (TO-92) plastic package intended for use in applications requiring enhanced noise immunity and direct interfacing to logic ICs and low power gate drivers.

## 2. Features and benefits

- Direct interfacing to logic level ICs
- Enhanced current surge capability
- Enhanced noise immunity
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- Very sensitive gate in four quadrants

## 3. Applications

- General purpose low power motor control
- Home appliances
- Industrial process control
- Low power AC Fan controllers

## 4. Quick reference data

Table 1. Quick reference data

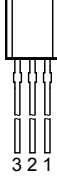
| Symbol                        | Parameter                            | Conditions                                                                                                                                                 | Min | Typ | Max  | Unit |
|-------------------------------|--------------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----|------|------|
| $V_{\text{DRM}}$              | repetitive peak off-state voltage    |                                                                                                                                                            | -   | -   | 800  | V    |
| $I_{\text{TSM}}$              | non-repetitive peak on-state current | full sine wave; $T_{\text{J}(\text{init})} = 25\text{ }^{\circ}\text{C}$ ; $t_{\text{p}} = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a> | -   | -   | 12.5 | A    |
| $I_{\text{T(RMS)}}$           | RMS on-state current                 | full sine wave; $T_{\text{lead}} \leq 45\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>               | -   | -   | 1    | A    |
| <b>Static characteristics</b> |                                      |                                                                                                                                                            |     |     |      |      |
| $I_{\text{GT}}$               | gate trigger current                 | $V_{\text{D}} = 12\text{ V}$ ; $I_{\text{T}} = 0.1\text{ A}$ ; T2+ G+; $T_{\text{J}} = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>                | 0.2 | -   | 3    | mA   |
|                               |                                      | $V_{\text{D}} = 12\text{ V}$ ; $I_{\text{T}} = 0.1\text{ A}$ ; T2+ G-; $T_{\text{J}} = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>                | 0.2 | -   | 3    | mA   |



| Symbol | Parameter | Conditions                                                                                                        | Min | Typ | Max | Unit |
|--------|-----------|-------------------------------------------------------------------------------------------------------------------|-----|-----|-----|------|
|        |           | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a> | 0.2 | -   | 3   | mA   |
|        |           | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a> | 0.2 | -   | 5   | mA   |

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description     | Simplified outline                                                                                 | Graphic symbol                                                                                |
|-----|--------|-----------------|----------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------|
| 1   | T2     | main terminal 2 | <br>TO-92 (SOT54) | <br>sym051 |
| 2   | G      | gate            |                                                                                                    |                                                                                               |
| 3   | T1     | main terminal 1 |                                                                                                    |                                                                                               |

## 6. Ordering information

Table 3. Ordering information

| Type number | Package |                                                             |         |
|-------------|---------|-------------------------------------------------------------|---------|
|             | Name    | Description                                                 | Version |
| Z0103NA0    | TO-92   | plastic single-ended leaded (through hole) package; 3 leads | SOT54   |

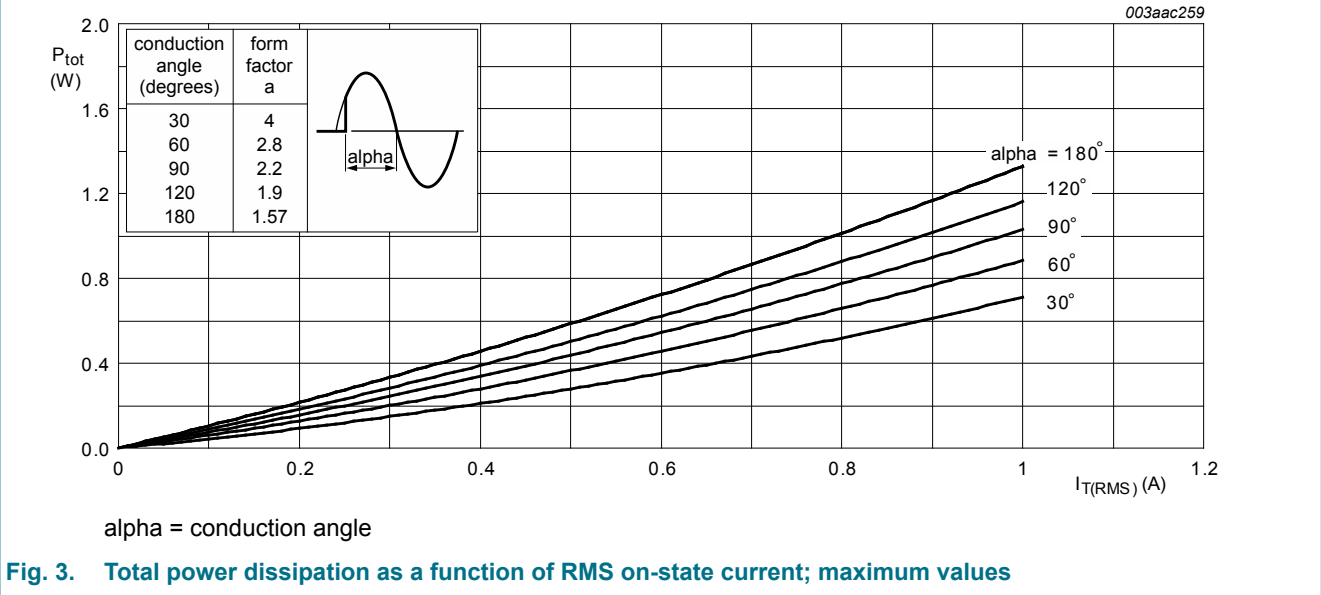
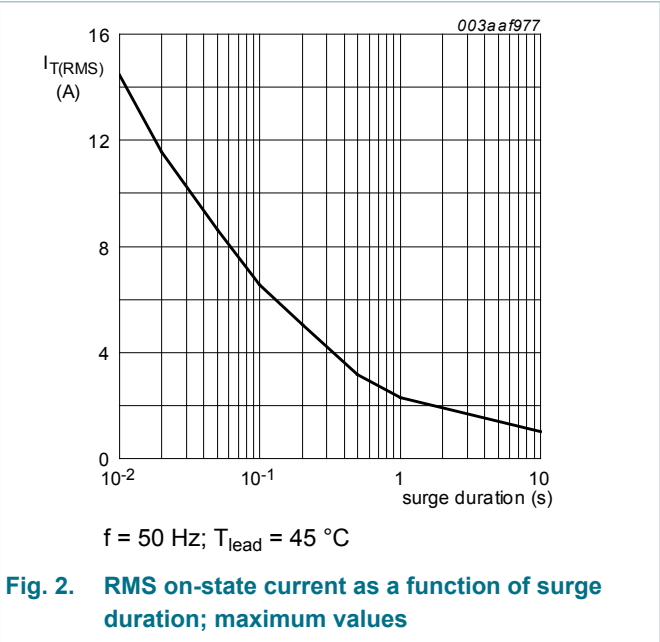
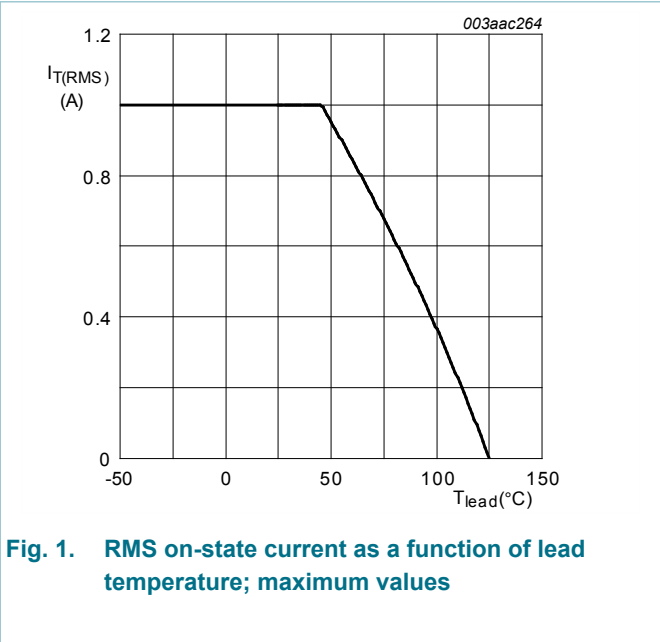
## 7. Limiting values

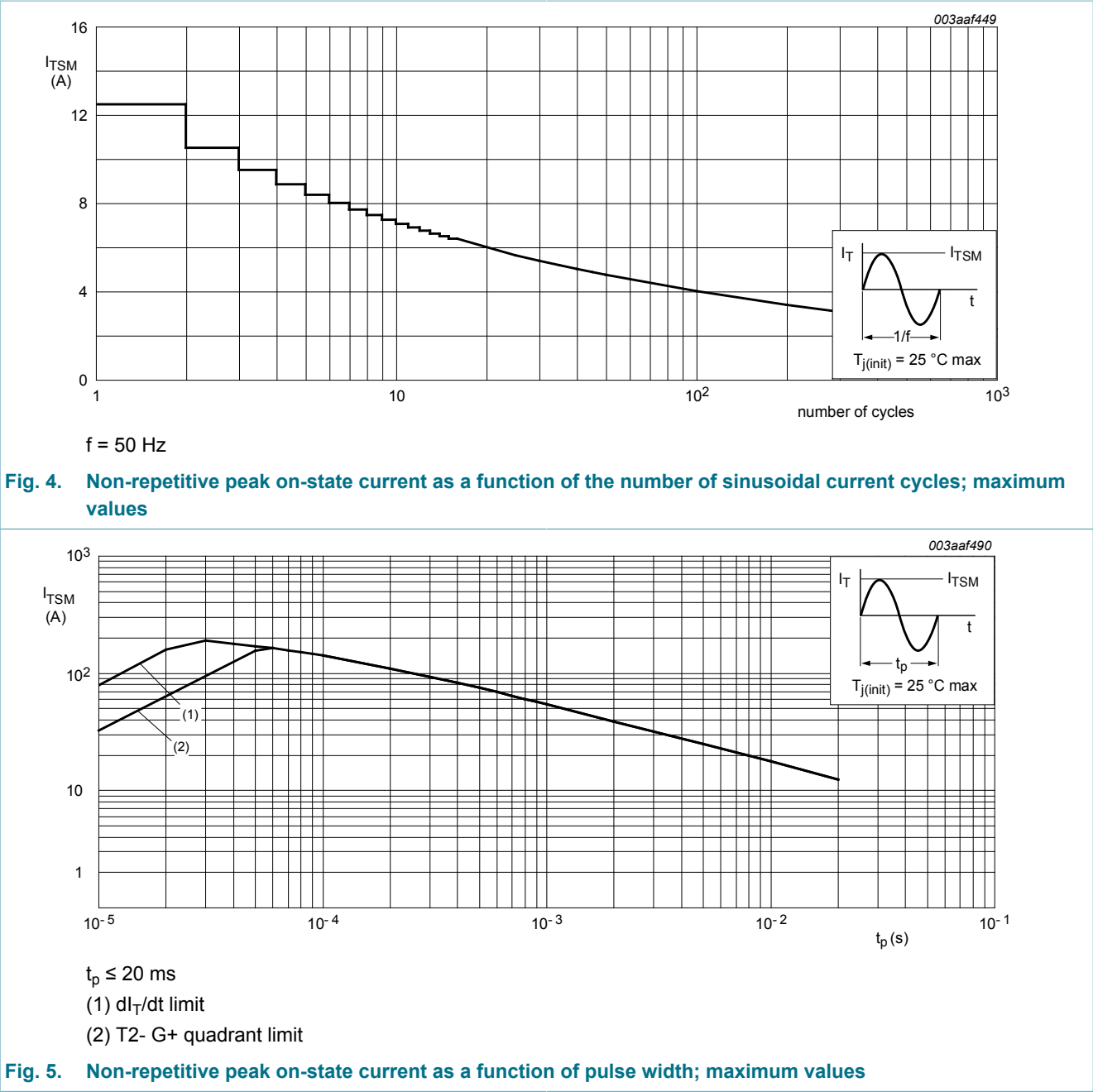
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol              | Parameter                            | Conditions                                                                                                                                    | Min | Max  | Unit             |
|---------------------|--------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------|-----|------|------------------|
| $V_{\text{DRM}}$    | repetitive peak off-state voltage    |                                                                                                                                               | -   | 800  | V                |
| $I_{\text{T(RMS)}}$ | RMS on-state current                 | full sine wave; $T_{\text{lead}} \leq 45\text{ }^\circ\text{C}$ ; <a href="#">Fig. 1</a> ;<br><a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a> | -   | 1    | A                |
| $I_{\text{TSM}}$    | non-repetitive peak on-state current | full sine wave; $T_{\text{j(init)}} = 25\text{ }^\circ\text{C}$ ;<br>$t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>   | -   | 12.5 | A                |
|                     |                                      | full sine wave; $T_{\text{j(init)}} = 25\text{ }^\circ\text{C}$ ;<br>$t_p = 16.7\text{ ms}$                                                   | -   | 13.8 | A                |
| $I^2t$              | $I^2t$ for fusing                    | $t_p = 10\text{ ms}$ ; SIN                                                                                                                    | -   | 0.78 | A <sup>2</sup> s |
| $di_T/dt$           | rate of rise of on-state current     | $I_T = 1\text{ A}$ ; $I_G = 20\text{ mA}$ ; $di_G/dt = 100\text{ mA}/\mu\text{s}$ ; T2+ G+                                                    | -   | 50   | A/ $\mu\text{s}$ |
|                     |                                      | $I_T = 1\text{ A}$ ; $I_G = 20\text{ mA}$ ; $di_G/dt = 100\text{ mA}/\mu\text{s}$ ; T2+ G-                                                    | -   | 50   | A/ $\mu\text{s}$ |

| Symbol      | Parameter            | Conditions                                                                                 |  | Min | Max | Unit               |
|-------------|----------------------|--------------------------------------------------------------------------------------------|--|-----|-----|--------------------|
|             |                      | $I_T = 1\text{ A}$ ; $I_G = 20\text{ mA}$ ; $dI_G/dt = 100\text{ mA}/\mu\text{s}$ ; T2- G- |  | -   | 50  | A/ $\mu\text{s}$   |
|             |                      | $I_T = 1\text{ A}$ ; $I_G = 20\text{ mA}$ ; $dI_G/dt = 100\text{ mA}/\mu\text{s}$ ; T2- G+ |  | -   | 20  | A/ $\mu\text{s}$   |
| $I_{GM}$    | peak gate current    |                                                                                            |  | -   | 1   | A                  |
| $P_{GM}$    | peak gate power      |                                                                                            |  | -   | 2   | W                  |
| $P_{G(AV)}$ | average gate power   | over any 20 ms period                                                                      |  | -   | 0.1 | W                  |
| $T_{stg}$   | storage temperature  |                                                                                            |  | -40 | 150 | $^{\circ}\text{C}$ |
| $T_j$       | junction temperature |                                                                                            |  | -   | 125 | $^{\circ}\text{C}$ |





8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol           | Parameter                                   | Conditions                                                  | Min | Typ | Max | Unit |
|------------------|---------------------------------------------|-------------------------------------------------------------|-----|-----|-----|------|
| $R_{th(j-lead)}$ | thermal resistance from junction to lead    | full cycle; <a href="#">Fig. 6</a>                          | -   | -   | 60  | K/W  |
| $R_{th(j-a)}$    | thermal resistance from junction to ambient | full cycle; printed circuit board mounted; lead length 4 mm | -   | 150 | -   | K/W  |

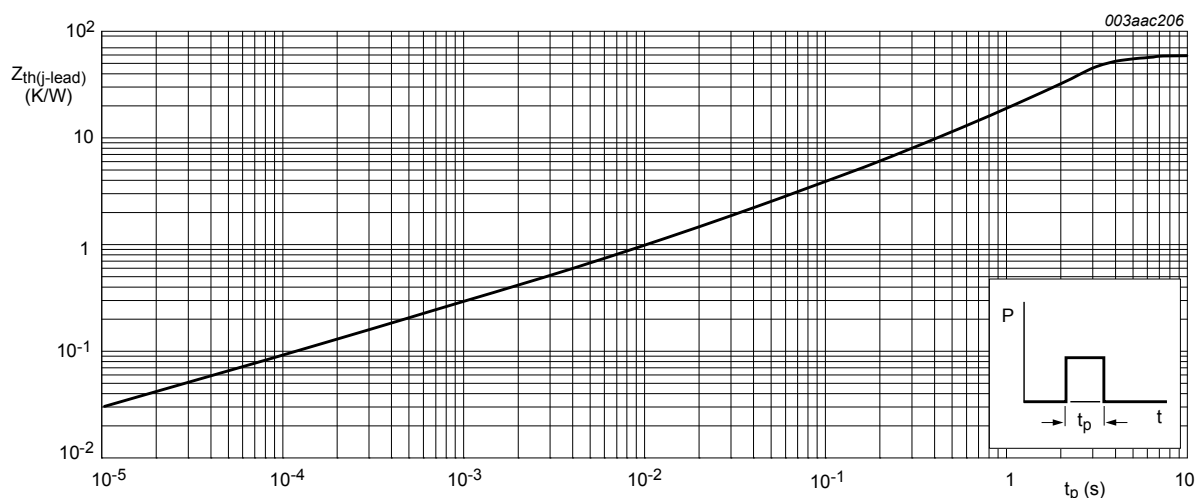


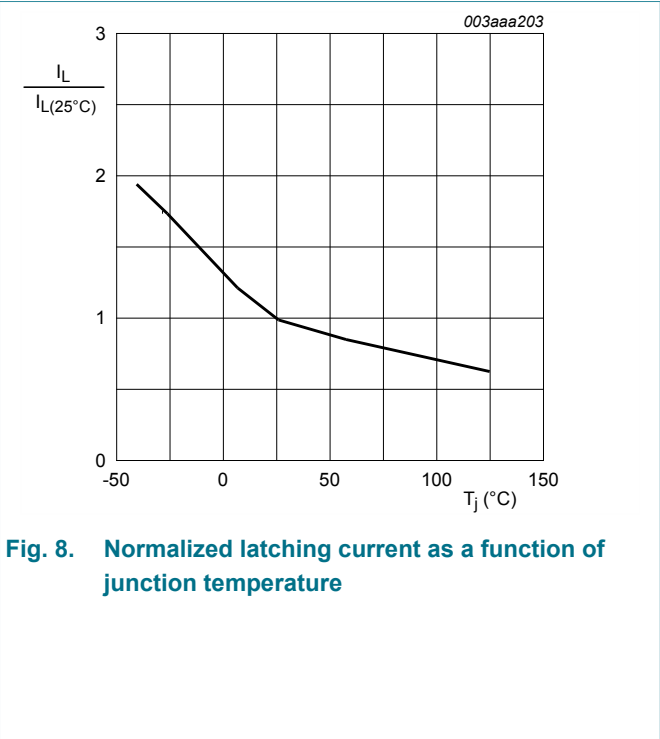
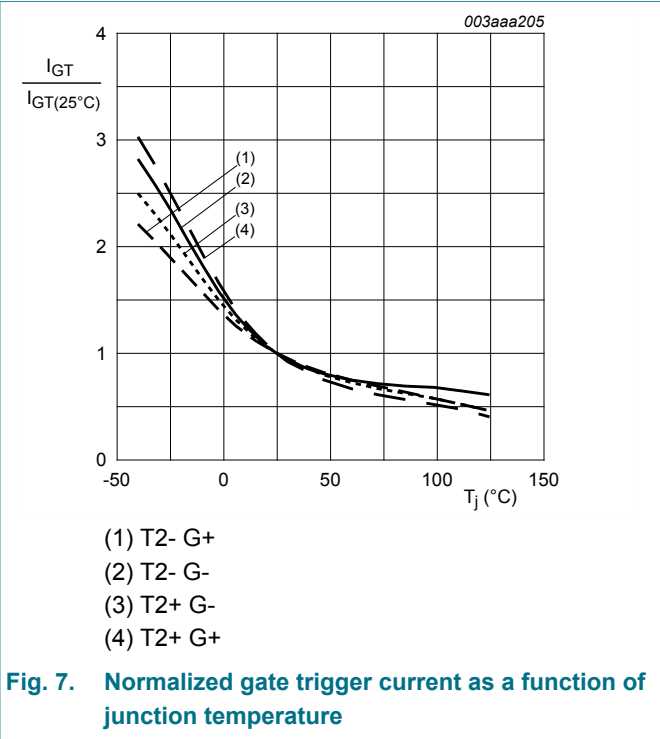
Fig. 6. Transient thermal impedance from junction to lead as a function of pulse width

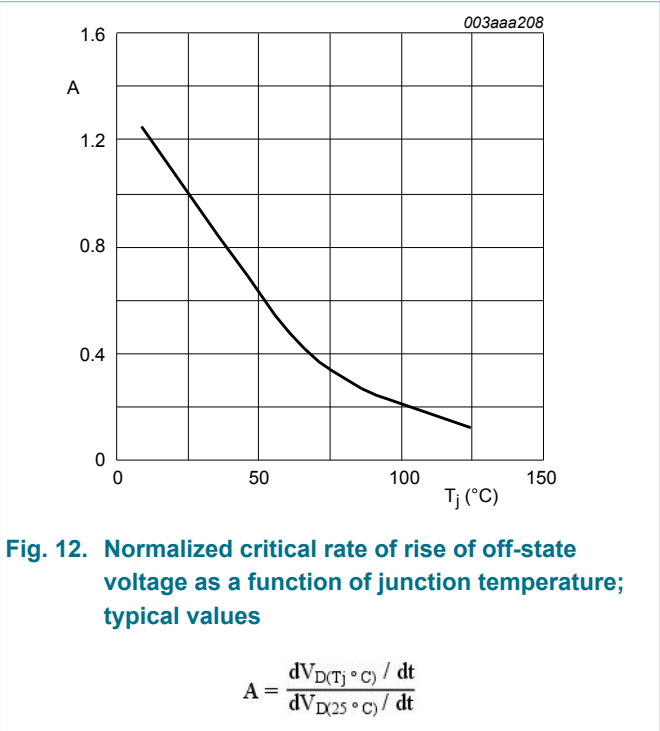
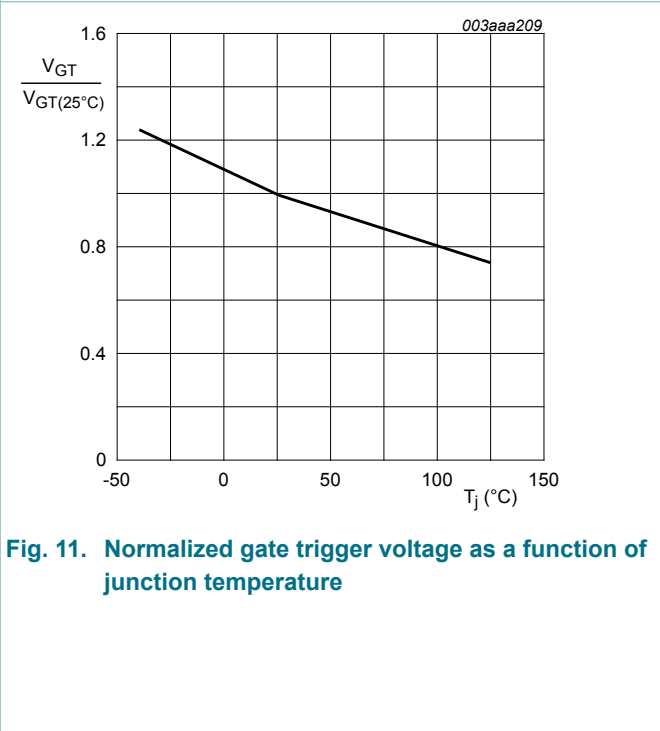
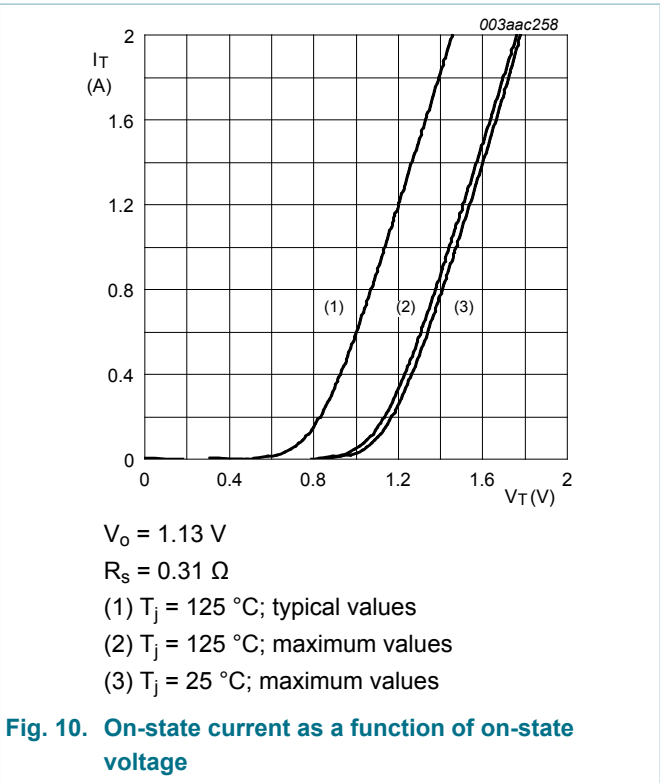
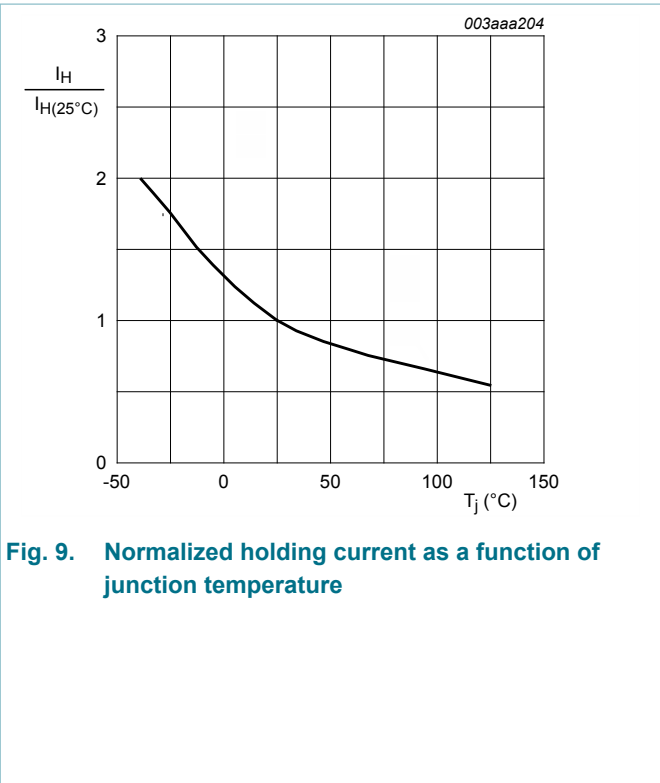
## 9. Characteristics

Table 6. Characteristics

| Symbol                        | Parameter            | Conditions                                                                                                        | Min | Typ | Max | Unit |
|-------------------------------|----------------------|-------------------------------------------------------------------------------------------------------------------|-----|-----|-----|------|
| <b>Static characteristics</b> |                      |                                                                                                                   |     |     |     |      |
| $I_{GT}$                      | gate trigger current | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+;<br>$T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a> | 0.2 | -   | 3   | mA   |
|                               |                      | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-;<br>$T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a> | 0.2 | -   | 3   | mA   |
|                               |                      | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-;<br>$T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a> | 0.2 | -   | 3   | mA   |
|                               |                      | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+;<br>$T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a> | 0.2 | -   | 5   | mA   |
| $I_L$                         | latching current     | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+;<br>$T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a> | -   | -   | 7   | mA   |
|                               |                      | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-;<br>$T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a> | -   | -   | 20  | mA   |
|                               |                      | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-;<br>$T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a> | -   | -   | 7   | mA   |
|                               |                      | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G+;<br>$T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a> | -   | -   | 7   | mA   |
| $I_H$                         | holding current      | $V_D = 12\text{ V}$ ; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>                                   | -   | -   | 7   | mA   |
| $V_T$                         | on-state voltage     | $I_T = 1\text{ A}$ ; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>                                   | -   | 1.3 | 1.6 | V    |
| $V_{GT}$                      | gate trigger voltage | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_J = 25\text{ }^\circ\text{C}$ ;<br><a href="#">Fig. 11</a>        | -   | -   | 1   | V    |

| Symbol                  | Parameter                             | Conditions                                                                                                                                                       |  | Min | Typ | Max | Unit             |
|-------------------------|---------------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------|--|-----|-----|-----|------------------|
|                         |                                       | $V_D = 800\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 125\text{ }^\circ\text{C}$ ;<br><a href="#">Fig. 11</a>                                                     |  | 0.2 | -   | -   | V                |
| $I_D$                   | off-state current                     | $V_D = 800\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$                                                                                                         |  | -   | -   | 0.5 | mA               |
| Dynamic characteristics |                                       |                                                                                                                                                                  |  |     |     |     |                  |
| $dV_D/dt$               | rate of rise of off-state voltage     | $V_{DM} = 536\text{ V}$ ; $T_j = 110\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit; <a href="#">Fig. 12</a> |  | 80  | -   | -   | V/ $\mu\text{s}$ |
| $dV_{com}/dt$           | rate of change of commutating voltage | $V_D = 400\text{ V}$ ; $T_j = 110\text{ }^\circ\text{C}$ ; $dI_{com}/dt = 0.44\text{ A/ms}$ ; gate open circuit                                                  |  | 0.5 | -   | -   | V/ $\mu\text{s}$ |





10. Package outline

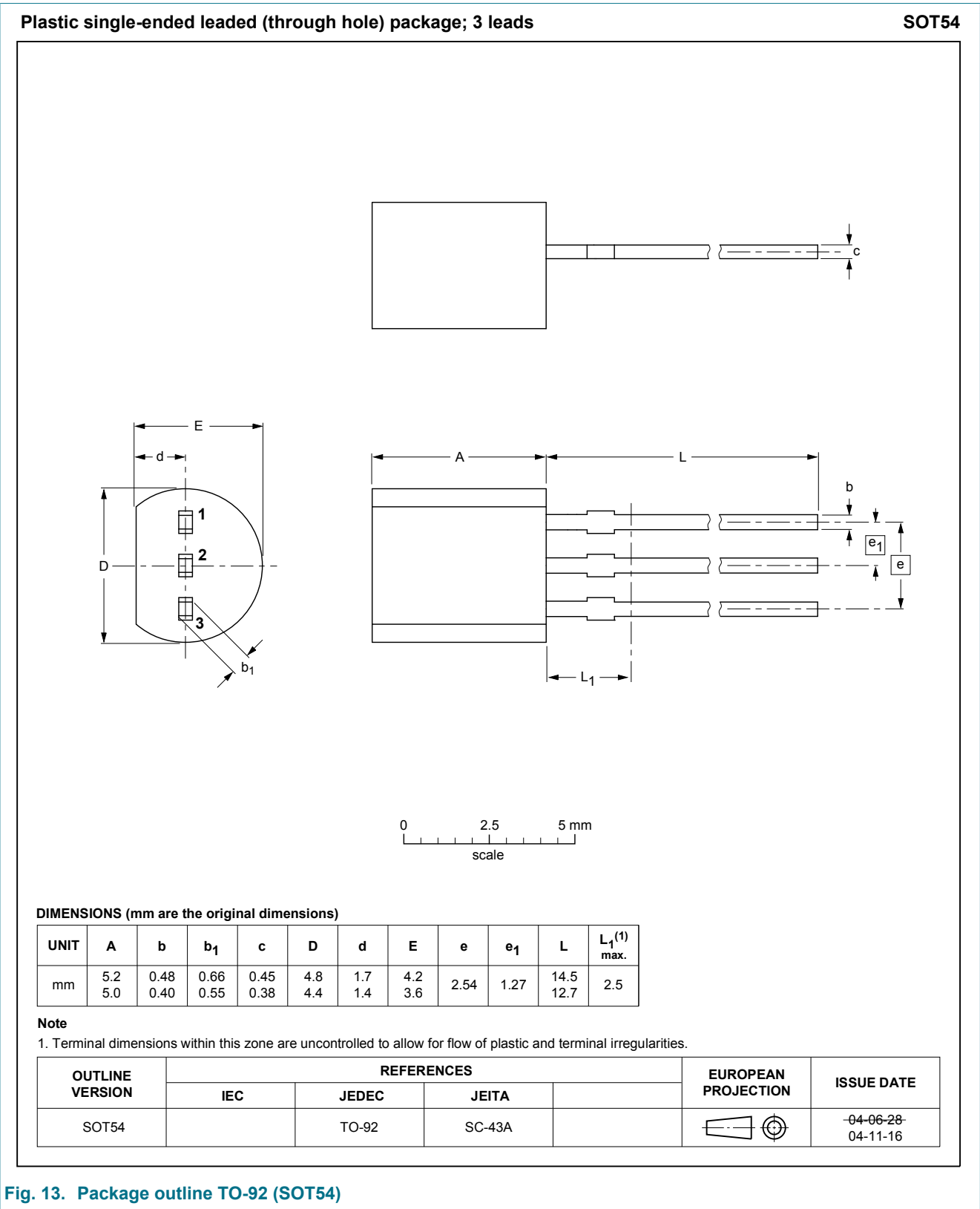


Fig. 13. Package outline TO-92 (SOT54)

## 11. Legal information

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| Document status [1][2]         | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
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- [1] Please consult the most recently issued document before initiating or completing a design.
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Date of release: 4 April 2014